

MICROCHIP 25AA080/25LC080/25C080

8K SPITM Bus Serial EEPROM

DEVICE SELECTION TABLE

Part Number	Vcc Range	Max Clock Frequency	Temp Ranges	
25C080	4.5-5.5V	3 MHz	C,I,E	
25LC080	2.5-5.5V	2 MHz	C,I	
25AA080	1.8-5.5V	1 MHz	C,I	

FEATURES

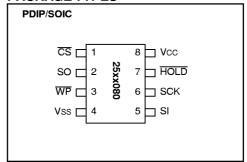
- · Low power CMOS technology
 - Write current: 3 mA maximum
 - Read current: 500 µA typical
 - Standby current: 500 nA typical
- 1024 x 8 bit organization
- · 16 byte page
- · Write cycle time: 5ms max.
- · Self-timed ERASE and WRITE cycles
- · Block write protection
 - Protect none, 1/4, 1/2, or all of array
- · Built-in write protection
 - Power on/off data protection circuitry
 - Write enable latch
- Write protect pin
- Sequential read
- High reliability
 - Endurance: 1M cycles (guaranteed)
 - Data retention: > 200 years
- ESD protection: > 4000 V
- 8-pin PDIP and SOIC
- · Temperature ranges supported.
 - Commercial (C): 0°C to +70°C Industrial (I): -40°C to +85°C Automotive (E) (25C080): -40°C to +125°C

DESCRIPTION

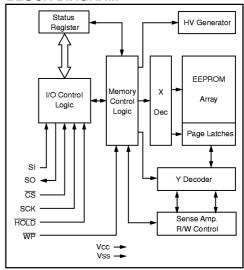
The Microchip Technology Inc. 25AA080/25LC080/25C080 (25xx080*) are 8K bit serial Electrically Erasable PROMs. The memory is accessed via a simple Serial Peripheral Interface (SPI) compatible serial bus. The bus signals required are a clock input (SCK) plus separate data in (SI) and data out (SO) lines. Access to the device is controlled through a chip select (CS) input.

Communication to the device can be paused via the hold pin (HOLD). While the device is paused, transitions on its inputs will be ignored, with the exception of chip select, allowing the host to service higher priority interrupts.

PACKAGE TYPES



BLOCK DIAGRAM



^{*25}xx080 is used in this document as a generic part number for the 25AA080/25LC080/25C080 devices. SPI is a trademark of Motorola.

1.0 ELECTRICAL CHARACTERISTICS

1.1 Maximum Ratings*

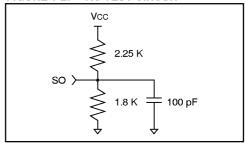
Vcc	7. 0V
All inputs and outputs w.r.t. Vss	0.6V to Vcc+1.0V
Storage temperature	65°C to 150°C
Ambient temperature under bias	65°C to 125°C
Soldering temperature of leads (10 second	nds)+300°C
ESD protection on all pins	4kV

*Notice: Stresses above those listed under 'Maximum ratings' may cause permanent damage to the device. This is a stress rating only and functional operation of the device at those or any other conditions above those indicated in the operational listings of this specification is not implied. Exposure to maximum rating conditions for an extended period of time may affect device reliability

TABLE 1-1: PIN FUNCTION TABLE

Name	Function
CS	Chip Select Input
so	Serial Data Output
SI	Serial Data Input
SCK	Serial Clock Input
WP	Write Protect Pin
Vss	Ground
Vcc	Supply Voltage
HOLD	Hold Input

FIGURE 1-2: AC TEST CIRCUIT



1.2 AC Test Conditions

AC Waveform:

VLO = 0.2V

VHI = VCC - 0.2V (Note 1) VHI = 4.0V (Note 2)

0.5 Vcc

Timing Measurement Reference Level Input 0.5 VCC

Output $\label{eq:output} \textbf{Note 1:} \ \ \text{For VCC} \leq 4.0V$

2: For VCC > 4.0V

TABLE 1-3: DC CHARACTERISTICS

All parameters apply over the specified operating ranges unless otherwise noted. Commercial (C): TAMB = 0°C to +70°C								
Parameter	Symbol	Min	Max	Units	Test Conditions			
High lovel input voltage	VIH1	2.0	Vcc+1	٧	Vcc ≥ 2.7V (Note)			
High level input voltage	VIH2	0.7 Vcc	Vcc+1	V	Vcc< 2.7V (Note)			
Low lovel input veltage	Vı∟1	-0.3	0.8	V	Vcc ≥ 2.7V (Note)			
Low level input voltage	VIL2	-0.3	0.3 Vcc	V	Vcc < 2.7V (Note)			
Low lovel output voltage	Vol	_	0.4	V	IOL = 2.1 mA			
Low level output voltage	Vol	_	0.2	V	IOL = 1.0 mA, VCC < 2.5V			
High level output voltage	Vон	Vcc -0.5	_	V	IOH =-400 μA			
Input leakage current	ILI	-10	10	μΑ	CS = Vcc, Vin = Vss to Vcc			
Output leakage current	ILO	-10	10	μΑ	CS = Vcc, Vout = Vss to Vcc			
Internal Capacitance (all inputs and outputs)	CINT	_	7	pF	TAMB = 25°C, CLK = 1.0 MHz, VCC = 5.0V (Note)			
Operating Current	Icc Read	_ _	1 500	mA μA	VCC = 5.5V; FCLK=3.0 MHz; SO = Open VCC = 2.5V; FCLK=2.0 MHz; SO = Open			
Operating Current	ICC Write	_ _	5 3	mA mA	VCC= 5.5V VCC = 2.5V			
Standby Current	Iccs	_	5 1	μA μA	\overline{CS} = Vcc = 5.5V, Inputs tied to Vcc or Vss \overline{CS} = Vcc = 2.5V, Inputs tied to Vcc or Vss			

Note: This parameter is periodically sampled and not 100% tested.

TABLE 1-4: AC CHARACTERISTICS

All parameters apply over the specified operating ranges	Commercial (C): Industrial (I):	Tamb = -4	°C to +70°C 10°C to +85°C	Vcc = 1.8 Vcc = 1.8	V to 5.5V
unless otherwise noted. Parameter	Automotive (E):	Min	10°C to +125°C	Units	Test Conditions
	FCLK		3	MHz	Vcc = 4.5V to 5.5V
Clock Frequency	FCLK	_	$\begin{bmatrix} 3 \\ 2 \end{bmatrix}$	MHz	VCC = 4.5V to 5.5V VCC = 2.5V to 4.5V
		_	1 1	MHz	Vcc = 1.8V to 2.5V
CS Setup Time	Tcss	100	 	ns	Vcc = 4.5V to 5.5V
OG Getup Time	1000	250	_	ns	Vcc = 2.5V to 4.5V
		500	_	ns	Vcc = 1.8V to 2.5V
CS Hold Time	TCSH	150	<u> </u>	ns	Vcc = 4.5V to 5.5V
Seriola Timo	10011	250	_	ns	Vcc = 2.5V to 4.5V
		475	-	ns	Vcc = 1.8V to 2.5V
CS Disable Time	Tcsp	500	_	ns	
Data Setup Time	Tsu	30		ns	Vcc = 4.5V to 5.5V
	.55	50	_	ns	Vcc = 2.5V to 4.5V
		50	_	ns	Vcc = 1.8V to 2.5V
Data Hold Time	THD	50		ns	Vcc = 4.5V to 5.5V
		100	_	ns	Vcc = 2.5V to 4.5V
		100	-	ns	Vcc = 1.8V to 2.5V
CLK Rise Time	TR	_	2	μs	(Note 1)
CLK Fall Time	TF		2	μs	(Note 1)
Clock High Time	Тні	150	t _ t	ns	Vcc = 4.5V to 5.5V
g		250	_	ns	Vcc = 2.5V to 4.5V
		475	-	ns	Vcc = 1.8V to 2.5V
Clock Low Time	TLO	150	_	ns	Vcc = 4.5V to 5.5V
		250	-	ns	Vcc = 2.5V to 4.5V
		475		ns	Vcc = 1.8V to 2.5V
Clock Delay Time	TCLD	50	_	ns	
Clock Enable Time	TCLE	50		ns	
Output Valid from	Tv	_	150	ns	Vcc = 4.5V to 5.5V
Clock Low		_	250	ns	Vcc = 2.5V to 4.5V
		_	475	ns	Vcc = 1.8V to 2.5V
Output Hold Time	Тно	0	_	ns	(Note 1)
Output Disable Time	Tois	_	200	ns	Vcc = 4.5V to 5.5V (Note 1)
		_	250	ns	Vcc = 2.5V to 4.5V (Note 1)
			500	ns	Vcc = 1.8V to 2.5V (Note 1)
HOLD Setup Time	THS	100	-	ns	Vcc = 4.5V to 5.5V
		100	-	ns	Vcc = 2.5V to 4.5V
		200		ns	Vcc = 1.8V to 2.5V
HOLD Hold Time	Тнн	100	-	ns	Vcc = 4.5V to 5.5V
		100	-	ns	Vcc = 2.5V to 4.5V
HOLD I COLUMN T	+ -	200	 	ns	Vcc = 1.8V to 2.5V
HOLD Low to Output High-Z	THZ	100	-	ns	Vcc = 4.5V to 5.5V (Note 1)
		150 200		ns ns	VCC = 2.5V to 4.5V (Note 1) VCC = 1.8V to 2.5V (Note 1)
HOLD High to Output Velid	Ting				, ,
HOLD High to Output Valid	THV	100 150	_	ns ns	VCC = 4.5V to 5.5V VCC = 2.5V to 4.5V
		200		ns	Vcc = 2.5V to 4.5V Vcc = 1.8V to 2.5V
Internal Write Cycle Time	Twc		5	ms	111 - 110 (10 2.0)
	1 440		 		(Nata 2)
Endurance	_	1M	-	E/W Cycles	(Note 2)

Note 1: This parameter is periodically sampled and not 100% tested.

^{2:} This parameter is not tested but guaranteed by characterization. For endurance estimates in a specific application, please consult the Total Endurance Model which can be obtained on our website.

FIGURE 1-5: HOLD TIMING

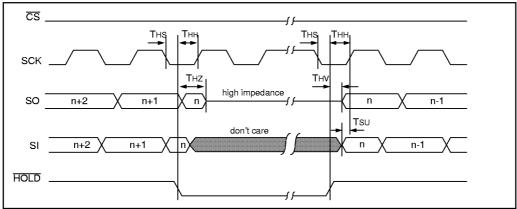


FIGURE 1-6: SERIAL INPUT TIMING

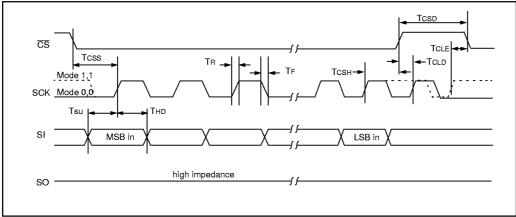
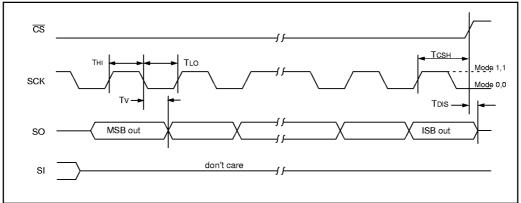


FIGURE 1-7: SERIAL OUTPUT TIMING



2.0 PIN DESCRIPTIONS

2.1 Chip Select (CS)

A low level on this pin selects the device. A high level deselects the device and forces it into standby mode. However, a programming cycle which is already initiated or in progress will be completed, regardless of the $\overline{\text{CS}}$ input signal. If $\overline{\text{CS}}$ is brought high during a program cycle, the device will go in standby mode as soon as the programming cycle is complete. As soon as the device is deselected, SO goes to the high impedance state, allowing multiple parts to share the same SPI bus. A low to high transition on $\overline{\text{CS}}$ after a valid write sequence initiates an internal write cycle. After power-up, a low level on $\overline{\text{CS}}$ is required prior to any sequence being initiated.

2.2 Serial Input (SI)

The SI pin is used to transfer data into the device. It receives instructions, addresses, and data. Data is latched on the rising edge of the serial clock.

2.3 Serial Output (SO)

The SO pin is used to transfer data out of the 25xx080. During a read cycle, data is shifted out on this pin after the falling edge of the serial clock.

2.4 Serial Clock (SCK)

The SCK is used to synchronize the communication between a master and the 25xx080. Instructions, addresses, or data present on the SI pin are latched on the rising edge of the clock input, while data on the SO pin is updated after the falling edge of the clock input.

2.5 Write Protect (WP)

This pin is used in conjunction with the WPEN bit in the status register to prohibit writes to the non-volatile bits in the status register. When \overline{WP} is low and WPEN is high, writing to the non-volatile bits in the status register is disabled. All other operations function normally. When \overline{WP} is high, all functions, including writes to the non-volatile bits in the status register operate normally. If the WPEN bit is set, \overline{WP} low during a status register write sequence will disable writing to the status register. If an internal write cycle has already begun, \overline{WP} going low will have no effect on the write.

The \overline{WP} pin function is blocked when the WPEN bit in the status register is low. This allows the user to install the 25xx080 in a system with \overline{WP} pin grounded and still be able to write to the status register. The \overline{WP} pin functions will be enabled when the WPEN bit is set high.

2.6 Hold (HOLD)

The HOLD pin is used to suspend transmission to the 25xx080 while in the middle of a serial sequence without having to re-transmit the entire sequence over at a later time. It must be held high any time this function is not being used. Once the device is selected and a serial sequence is underway, the HOLD pin may be pulled low to pause further serial communication without resetting the serial sequence. The HOLD pin must be brought low while SCK is low, otherwise the HOLD function will not be invoked until the next SCK high to low transition. The 25xx080 must remain selected during this sequence. The SI, SCK, and SO pins are in a high impedance state during the time the part is paused and transitions on these pins will be ignored. To resume serial communication, HOLD must be brought high while the SCK pin is low, otherwise serial communication will not resume. Lowering the HOLD line at any time will tri-state the SO line.

3.0 FUNCTIONAL DESCRIPTION

3.1 PRINCIPLES OF OPERATION

The 25xx080 are 1024 byte Serial EEPROMs designed to interface directly with the Serial Peripheral Interface (SPI) port of many of today's popular microcontroller families, including Microchip's PIC16C6X/7X microcontrollers. It may also interface with microcontrollers that do not have a built-in SPI port by using discrete I/O lines programmed properly with the software.

The 25xx080 contains an 8-bit instruction register. The part is accessed via the SI pin, with data being clocked in on the rising edge of SCK. The \overline{CS} pin must be low and the \overline{HOLD} pin must be high for the entire operation. The \overline{WP} pin must be held high to allow writing to the memory array.

Table 3-1 contains a list of the possible instruction bytes and format for device operation. All instructions, addresses, and data are transferred MSB first, LSB last

Data is sampled on the first rising edge of SCK after CS goes low. If the clock line is shared with other peripheral devices on the SPI bus, the user can assert the HOLD input and place the 25xx080 in 'HOLD' mode. After releasing the HOLD pin, operation will resume from the point when the HOLD was asserted.

3.2 Read Sequence

The part is selected by pulling $\overline{\text{CS}}$ low. The 8-bit read instruction is transmitted to the 25xx080 followed by the 16-bit address, with the six MSBs of the address being don't care bits. After the correct read instruction and address are sent, the data stored in the memory at the selected address is shifted out on the SO pin. The data stored in the memory at the next address can be read sequentially by continuing to provide clock pulses. The internal address pointer is automatically incremented to the next higher address after each byte of data is shifted out. When the highest address is reached (03FFh), the address counter rolls over to address 0000h allowing the read cycle to be continued indefinitely. The read operation is terminated by raising the $\overline{\text{CS}}$ pin (Figure 3-2).

3.3 Write Sequence

Prior to any attempt to write data to the 25xx080, the write enable latch must be set by issuing the WREN instruction (Figure 3-5). This is done by setting \overline{CS} low and then clocking out the proper instruction into the 25xx080. After all eight bits of the instruction are transmitted, the \overline{CS} must be brought high to set the write enable latch. If the write operation is initiated immediately after the WREN instruction without \overline{CS} being brought high, the data will not be written to the array because the write enable latch will not have been properly set.

Once the write enable latch is set, the user may proceed by setting the $\overline{\text{CS}}$ low, issuing a write instruction, followed by the 16-bit address, with the six MSBs of the address being don't care bits, and then the data to be written. Up to 16 bytes of data can be sent to the 25xx080 before a write cycle is necessary. The only restriction is that all of the bytes must reside in the same page. A page address begins with XXXX XXXX XXXX XXXX 0000 and ends with XXXX XXXX XXXX 1111. If the internal address counter reaches XXXX XXXX XXXX XXXX 1111 and the clock continues, the counter will roll back to the first address of the page and overwrite any data in the page that may have been written.

For the data to be actually written to the array, the $\overline{\text{CS}}$ must be brought high after the least significant bit (D0) of the nth data byte has been clocked in. If $\overline{\text{CS}}$ is brought high at any other time, the write operation will not be completed. Refer to Figure 3-3 and Figure 3-4 for more detailed illustrations on the byte write sequence and the page write sequence respectively. While the write is in progress, the status register may be read to check the status of the WPEN, WIP, WEL, BP1, and BP0 bits (Figure 3-7). A read attempt of a memory array location will not be possible during a write cycle. When the write cycle is completed, the write enable latch is reset.

TABLE 3-1: INSTRUCTION SET

Instruction Name	Instruction Format	Description
READ	0000 0011	Read data from memory array beginning at selected address
WRITE	0000 0010	Write data to memory array beginning at selected address
WRDI	0000 0100	Reset the write enable latch (disable write operations)
WREN	0000 0110	Set the write enable latch (enable write operations)
RDSR	0000 0101	Read status register
WRSR	0000 0001	Write status register

FIGURE 3-2: READ SEQUENCE

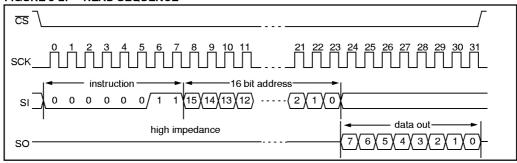


FIGURE 3-3: BYTE WRITE SEQUENCE

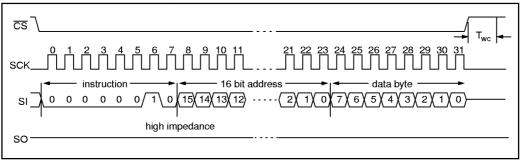
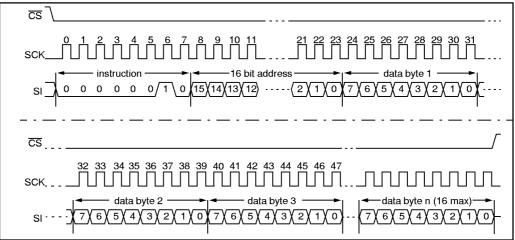


FIGURE 3-4: PAGE WRITE SEQUENCE



3.4 Write Enable (WREN) and Write Disable (WRDI)

The 25xx080 contains a write enable latch. See Table 3-10 for the Write Protect Functionality Matrix. This latch must be set before any write operation will be completed internally. The WREN instruction will set the latch, and the WRDI will reset the latch.

The following is a list of conditions under which the write enable latch will be reset:

- Power-up
- · WRDI instruction successfully executed
- · WRSR instruction successfully executed
- WRITE instruction successfully executed

FIGURE 3-5: WRITE ENABLE SEQUENCE

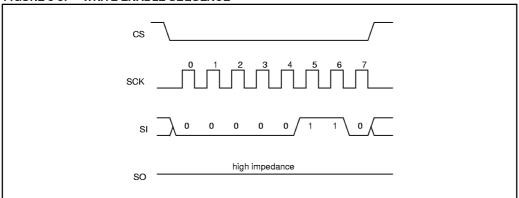
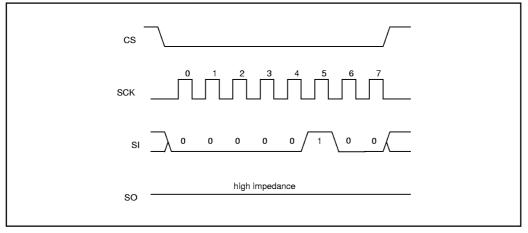


FIGURE 3-6: WRITE DISABLE SEQUENCE



3.5 Read Status Register (RDSR)

The RDSR instruction provides access to the status register. The status register may be read at any time, even during a write cycle. The status register is formatted as follows:

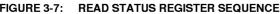
7	6	5	4	3	2	1	0
WPEN	Х	Х	Х	BP1	BP0	WEL	WIP

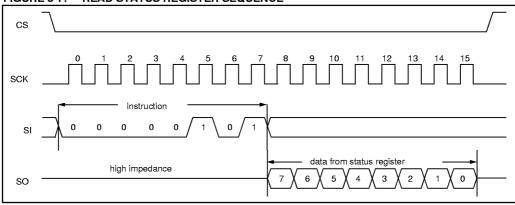
The **Write-In-Process (WIP)** bit indicates whether the 25xx080 is busy with a write operation. When set to a '1' a write is in progress, when set to a '0' no write is in progress. This bit is read only.

The **Write Enable Latch (WEL)** bit indicates the status of the write enable latch. When set to a '1' the latch allows writes to the array, when set to a '0' the latch prohibits writes to the array. The state of this bit can always be updated via the WREN or WRDI commands regardless of the state of write protection on the status register. This bit is read only.

The **Block Protection (BP0 and BP1)** bits indicate which blocks are currently write protected. These bits are set by the user issuing the WRSR instruction. These bits are non-volatile.

See Figure 3-7 for the RDSR timing sequence.





3.6 Write Status Register(WRSR)

The WRSR instruction allows the user to select one of four levels of protection for the array by writing to the appropriate bits in the status register. The array is divided up into four segments. The user has the ability to write protect none, one, two, or all four of the segments of the array. The partitioning is controlled as illustrated in Table 3-8.

The Write Protect Enable (WPEN) bit is a non-volatile bit that is available as an enable bit for the \overline{WP} pin. The Write Protect (\overline{WP}) pin and the Write Protect Enable (WPEN) bit in the status register control the programmable hardware write protect feature. Hardware write protection is enabled when \overline{WP} pin is low and the WPEN bit is high. Hardware write protection is disabled when either the \overline{WP} pin is high or the WPEN bit is low. When the chip is hardware write protected, only

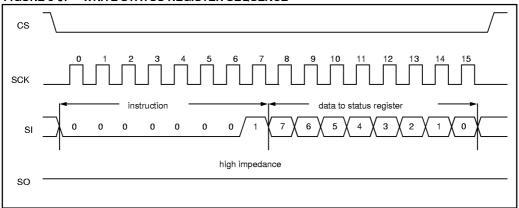
writes to non-volatile bits in the status register are disabled. See Table 3-3 for a matrix of functionality on the WPEN bit.

See Figure 3-9 for the WRSR timing sequence.

TABLE 3-8: ARRAY PROTECTION

BP1	BP0	Array Addresses Write Protected
0	0	none
0	1	upper 1/4 (0300h - 03FFh)
1	0	upper 1/2 (0200h - 03FFh)
1	1	all (0000h - 03FFh)

FIGURE 3-9: WRITE STATUS REGISTER SEQUENCE



3.7 <u>Data Protection</u>

The following protection has been implemented to prevent inadvertent writes to the array:

- · The write enable latch is reset on power-up.
- A write enable instruction must be issued to set the write enable latch.
- After a byte write, page write, or status register write, the write enable latch is reset.
- CS must be set high after the proper number of clock cycles to start an internal write cycle.
- Access to the array during an internal write cycle is ignored and programming is continued.

3.8 Power On State

The 25xx080 powers on in the following state:

- The device is in low power standby mode (CS = 1).
- · The write enable latch is reset.
- · SO is in high impedance state.
- A high to low level transition on CS is required to enter active state.

TABLE 3-10: WRITE PROTECT FUNCTIONALITY MATRIX

WPEN	WP	WEL	Protected Blocks	Unprotected Blocks	Status Register
Х	Х	0	Protected	Protected	Protected
0	Х	1	1 Protected W		Writable
1	Low	1	Protected	Writable	Protected
Х	High	1	Protected	Writable	Writable

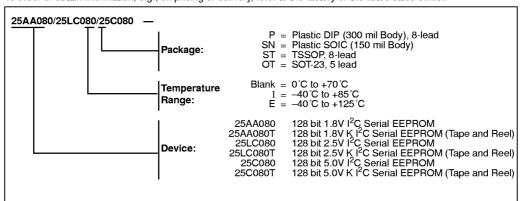
NOTES:

N		т	EC	
n	IL 1		-:>	•

NOTES:

25AA080/25LC080/25C080 PRODUCT IDENTIFICATION SYSTEM

To order or obtain information, e.g., on pricing or delivery, refer to the factory or the listed sales office..



Sales and Support

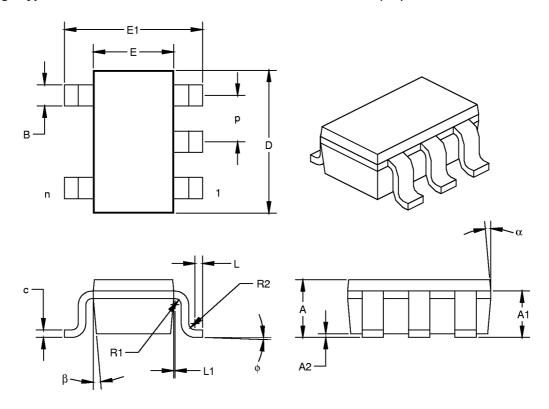
Data Sheets

Products supported by a preliminary Data Sheet may have an errata sheet describing minor operational differences and recommended workarounds. To determine if an errata sheet exists for a particular device, please contact one of the following:

- Your local Microchip sales office
- The Microchip Corporate Literature Center U.S. FAX: (602) 786-7277
 The Microchip's Bulletin Board, via your local CompuServe number (CompuServe membership NOT required).
 Please specify which device, revision of silicon and Data Sheet (include Literature #) you are using.



Package Type: K04-091 5-Lead Plastic Small Outline Transistor (OT)



Units		INCHES*			MILLIMETERS		
Dimension Limits		MIN	NOM	MAX	MIN	NOM	MAX
Pitch	р		0.037			0.95	
Number of Pins	n		5			5	
Overall Pack. Height	Α	0.035	0.046	0.057	0.90	1.18	1.45
Shoulder Height	A1	0.027	0.037	0.047	0.69	0.94	1.19
Standoff	A2	0.000	0.003	0.006	0.00	0.08	0.15
Molded Package Length	D [‡]	0.110	0.114	0.118	2.80	2.90	3.00
Molded Package Width	E [‡]	0.059	0.064	0.069	1.50	1.63	1.75
Outside Dimension	E1	0.102	0.110	0.118	2.60	2.80	3.00
Shoulder Radius	R1	0.005	0.005	0.010	0.13	0.13	0.25
Gull Wing Radius	R2	0.005	0.005	0.010	0.13	0.13	0.25
Foot Length	L	0.004	0.014	0.024	0.10	0.35	0.60
Foot Angle	ф	0	5	10	0	5	10
Radius Centerline	L1	0.000	0.001	0.005	0.00	0.03	0.13
Lead Thickness	С	0.004	0.006	0.008	0.09	0.15	0.20
Lower Lead Width	B [†]	0.014	0.017	0.020	0.35	0.43	0.50
Mold Draft Angle Top	α	0	5	10	0	5	10
Mold Draft Angle Bottom	β	0	5	10	0	5	10

^{*} Controlling Parameter.

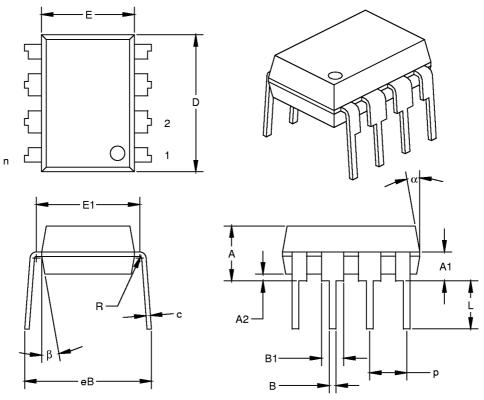
JEDEC equivalent: MO-178 AA

[†] Dimension "B" does not include dam-bar protrusions. Dam-bar protrusions shall not exceed 0.003" (0.076 mm) per side or 0.006" (0.152 mm) more than dimension "B."

[‡] Dimensions "D" and "E" do not include mold flash or protrusions. Mold flash or protrusions shall not exceed 0.010" (0.254 mm) per side or 0.020" (0.508 mm) more than dimensions "D" or "E."



Package Type: K04-018 8-Lead Plastic Dual In-line (P) - 300 mil



Units			INCHES*		М	ILLIMETER	S
Dimension Limits		MIN	NOM	MAX	MIN	NOM	MAX
PCB Row Spacing			0.300			7.62	
Number of Pins	n		8			8	
Pitch	р		0.100			2.54	
Lower Lead Width	В	0.014	0.018	0.022	0.36	0.46	0.56
Upper Lead Width	B1 [†]	0.055	0.060	0.065	1.40	1.52	1.65
Shoulder Radius	R	0.000	0.005	0.010	0.00	0.13	0.25
Lead Thickness	С	0.006	0.012	0.015	0.20	0.29	0.38
Top to Seating Plane	Α	0.140	0.150	0.160	3.56	3.81	4.06
Top of Lead to Seating Plane	A1	0.060	0.080	0.100	1.52	2.03	2.54
Base to Seating Plane	A2	0.005	0.020	0.035	0.13	0.51	0.89
Tip to Seating Plane	L	0.120	0.130	0.140	3.05	3.30	3.56
Package Length	D‡	0.355	0.370	0.385	9.02	9.40	9.78
Molded Package Width	E [‡]	0.245	0.250	0.260	6.22	6.35	6.60
Radius to Radius Width	E1	0.267	0.280	0.292	6.78	7.10	7.42
Overall Row Spacing	eВ	0.310	0.342	0.380	7.87	8.67	9.65
Mold Draft Angle Top	α	5	10	15	5	10	15
Mold Draft Angle Bottom	β	5	10	15	5	10	15

^{*} Controlling Parameter.

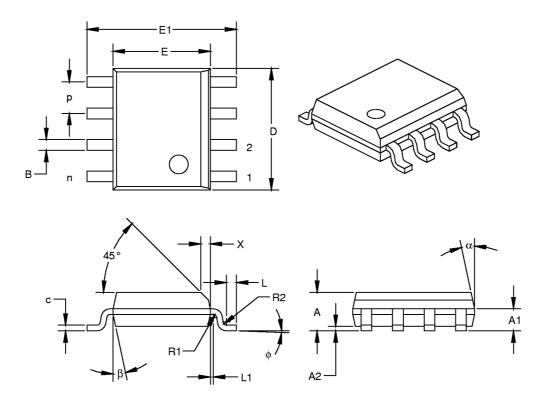
JEDEC equivalent: MS-001 BA

[†] Dimension "B1" does not include dam-bar protrusions. Dam-bar protrusions shall not exceed 0.003" (0.076 mm) per side or 0.006" (0.152 mm) more than dimension "B1."

[‡] Dimensions "D" and "E" do not include mold flash or protrusions. Mold flash or protrusions shall not exceed 0.010" (0.254 mm) per side or 0.020" (0.508 mm) more than dimensions "D" or "E."



Package Type: K04-057 8-Lead Plastic Small Outline (SN) - Narrow, 150 mil



Units		INCHES*			MILLIMETERS		
Dimension Limits		MIN	MOM	MAX	MIN	NOM	MAX
Pitch	р		0.050			1.27	
Number of Pins	n		8			8	
Overall Pack. Height	Α	0.054	0.061	0.069	1.37	1.56	1.75
Shoulder Height	A1	0.027	0.035	0.044	0.69	0.90	1.11
Standoff	A2	0.004	0.007	0.010	0.10	0.18	0.25
Molded Package Length	D [‡]	0.189	0.193	0.196	4.80	4.89	4.98
Molded Package Width	E [‡]	0.150	0.154	0.157	3.81	3.90	3.99
Outside Dimension	E1	0.229	0.237	0.244	5.82	6.01	6.20
Chamfer Distance	X	0.010	0.015	0.020	0.25	0.38	0.51
Shoulder Radius	R1	0.005	0.005	0.010	0.13	0.13	0.25
Gull Wing Radius	R2	0.005	0.005	0.010	0.13	0.13	0.25
Foot Length	L	0.011	0.016	0.021	0.28	0.41	0.53
Foot Angle	ф	0	4	8	0	4	8
Radius Centerline	L1	0.000	0.005	0.010	0.00	0.13	0.25
Lead Thickness	С	0.008	0.009	0.010	0.19	0.22	0.25
Lower Lead Width	B [†]	0.014	0.017	0.020	0.36	0.43	0.51
Mold Draft Angle Top	α	0	12	15	0	12	15
Mold Draft Angle Bottom	β	0	12	15	0	12	15

^{*} Controlling Parameter.

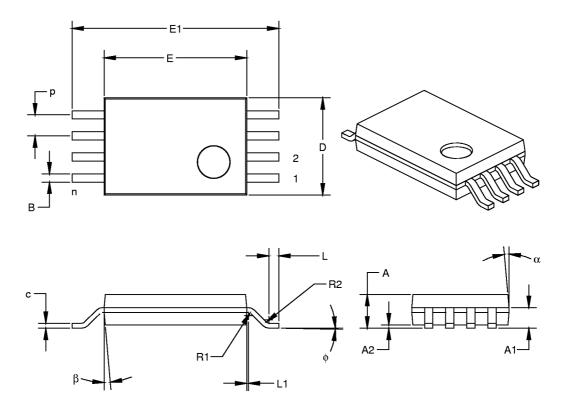
JEDEC equivalent: MS-012 AA

[†] Dimension "B" does not include dam-bar protrusions. Dam-bar protrusions shall not exceed 0.003" (0.076 mm) per side or 0.006" (0.152 mm) more than dimension "B."

[‡] Dimensions "D" and "E" do not include mold flash or protrusions. Mold flash or protrusions shall not exceed 0.010" (0.254 mm) per side or 0.020" (0.508 mm) more than dimensions "D" or "E."



Package Type: K04-086 8-Lead Plastic Thin Shrink Small Outline (ST) – 4.4 mm



Units		INCHES			MILLIMETERS*		
Dimension Limits		MIN	NOM	MAX	MIN	NOM	MAX
Pitch	р		0.026			0.65	
Number of Pins	n		8			8	
Overall Package Height	Α	0.039	0.041	0.043	1.00	1.05	1.10
Shoulder Height	A1	0.020	0.025	0.030	0.51	0.64	0.76
Standoff	A2	0.002	0.004	0.006	0.05	0.10	0.15
Molded Package Length	D [‡]	0.114	0.118	0.122	2.90	3.00	3.10
Molded Package Width	E [‡]	0.169	0.173	0.177	4.30	4.40	4.50
Outside Dimension	E1	0.246	0.251	0.256	6.25	6.38	6.50
Shoulder Radius	R1	0.000	0.004	0.010	0.00	0.10	0.25
Gull Wing Radius	R2	0.000	0.004	0.010	0.00	0.10	0.25
Foot Length	L	0.007	0.012	0.017	0.18	0.30	0.43
Foot Angle	ф	0	4	8	0	4	8
Radius Centerline	L1	0.000	0.002	0.005	0.00	0.05	0.13
Lead Thickness	С	0.004	0.006	0.008	0.09	0.15	0.20
Lower Lead Width	B [†]	0.007	0.010	0.012	0.19	0.25	0.30
Mold Draft Angle Top	α	0	5	10	0	5	10
Mold Draft Angle Bottom	β	0	5	10	0	5	10

^{*} Controlling Parameter.

JEDEC equivalent: MO-153 AA

[†] Dimension "B" does not include dam-bar protrusions. Dam-bar protrusions shall not exceed 0.003" (0.076 mm) per side or 0.006" (0.152 mm) more than dimension "B."

[‡] Dimensions "D" and "E" do not include mold flash or protrusions. Mold flash or protrusions shall not exceed 0.010" (0.254 mm) per side or 0.020" (0.508 mm) more than dimensions "D" or "E."